

PHOTOTRANSISTOR

KP-1608P1C WATER CLEAR LENS

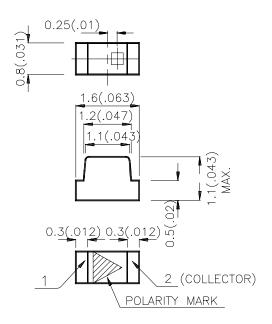
Features

- •MECHANICALLY AND SPECTRALLY MATCHED TO
- THE KP-1608 SERIES INFRARED EMITTING LED LAMP.
- •WATER CLEAR LENS.
- •PACKAGE:2000PCS/REEL.

Description

Made with NPN silicon phototransistor chips.

Package Dimensions



Notes:

- 1. All dimensions are in millimeters (inches).
- 2. Tolerance is $\pm 0.1(0.004")$ unless otherwise noted.
- 3. Lead spacing is measured where the lead emerge package.
- 4. Specifications are subject to change without notice.

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Absolute Maximum Rating at T_A=25°C

Parameter	Max. Ratings			
Collector-to-Emitter Breakdown Voltage	30V			
Emitter-to-Collector Breakdown Voltage	5V			
Power Dissipation at (or below) 25°C Free Air Temperature	100mW			
Operating Temperature Range	-40°C ~ +85°C			
Storage Temperature Range	-40°C ~ +85°C			

Electrical And Radiant Characteristics at T_A=25°C

Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Condiction
V _{BR CEO}	Collector-to-Emitter Breakdown Voltage	30	-	-	V	I _c =100uA, E _e =0mW/cm²
V _{BRECO}	Emitter-to-Collector Breakdown Voltage	5	-	-	V	I _E =100uA, E _e =0mW/cm²
V _{CE (SAT)}	Collector-to-Emitter Saturation Voltage	-	-	0.8	V	I _c =2mA, E _e =20mW/cm ²
I _{CEO}	Collector Dark Current	-	-	100	nA	V _{CE} =10V, E _e =0mW/cm²
T _R	Rise Time (10% to 90%)	-	3	-	us	V _{ce} =5V, I _c =1mA,
T _F	Fall Time (90% to 10%)	-	3	-	us	R _L =1000Ω
I _(ON)	On State Collector Current	0.1	0.3	-	mA	V _{ce} =5V, Ee=1mW/cm², λ=940nm

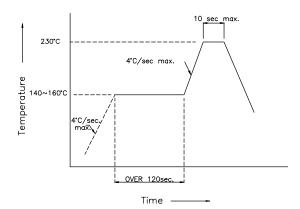
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Kingbright

KP-1608P1C

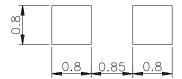
SMT Reflow Soldering Instructions

Number of reflow process shall be less than 2 times and cooling process to normal temperature is required between first and second soldering process.



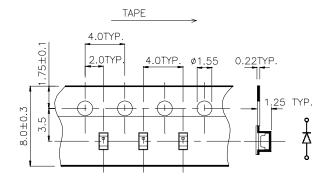
Recommended Soldering Pattern

(Units: mm)



Tape Specifications

(Units : mm)



SPEC NO: KDA0532 APPROVED:J.LU REV NO: V.1 CHECKED: DATE: SEP/17/2001 DRAWN:X.Q.ZHENG PAGE: 3 OF 3